

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _c = +25°C
60V	23mΩ @ V _{GS} = 10V	55A
	28mΩ @ V _{GS} = 4.5V	48A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Driving solenoids
- Driving relays
- Power-management functions

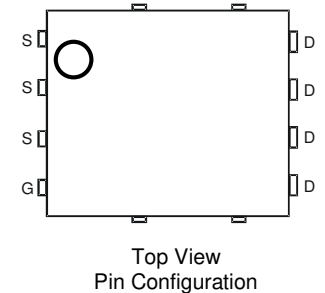
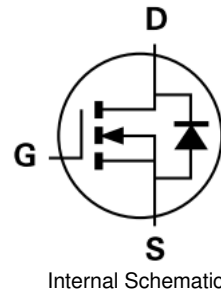
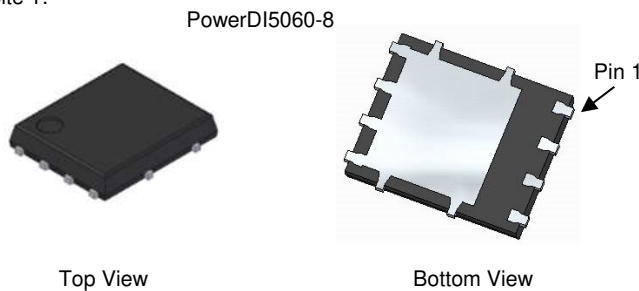
Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low R_{DS(ON)} – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMNH6021SPSQ](#))**

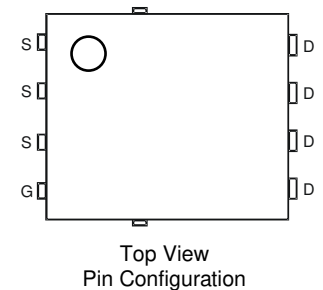
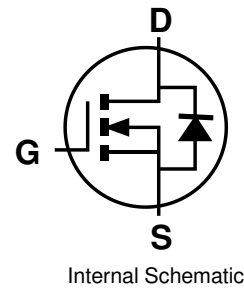
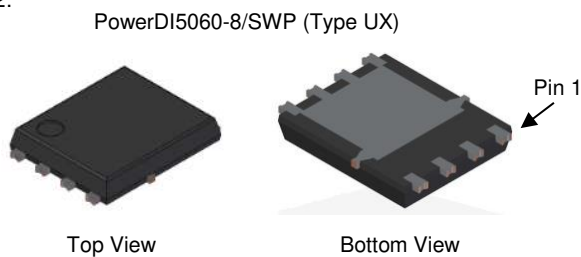
Mechanical Data

- Package: PowerDI®5060-8
- Package Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

Site 1:



Site 2:

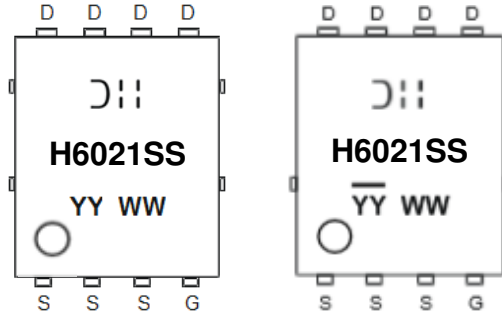


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMNH6021SPS-13	PowerDI5060-8	2,500	Tape & Reel
	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



☺|| = Manufacturer's Marking
 H6021SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 23 = 2023)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 5)	I _D	T _C = +25°C	55
		T _C = +100°C	39
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	55	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	88	A
Avalanche Current, L = 0.1mH (Note 6)	I _{AS}	35	A
Avalanche Energy, L = 0.1mH (Note 6)	E _{AS}	64	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 7)	P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	96	°C/W
Total Power Dissipation (Note 8)	P _D	3.0	W
Thermal Resistance, Junction to Ambient (Note 8)	R _{θJA}	50	°C/W
Total Power Dissipation (Note 5)	P _D	53	W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	1.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

- Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 7. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 8. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12	23	mΩ	V _{GS} = 10V, I _D = 12A
		—	18	28		V _{GS} = 4.5V, I _D = 12A
Diode Forward Voltage	V _{SD}	—	0.75	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1,016	—	pF	V _{DS} = 30V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	153	—		
Reverse Transfer Capacitance	C _{rss}	—	76.8	—		
Gate Resistance	R _g	—	2.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	9.5	—	nC	V _{DS} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	19.7	—		
Gate-Source Charge	Q _{gs}	—	3.6	—		
Gate-Drain Charge	Q _{gd}	—	4.8	—		
Turn-On Delay Time	t _{D(ON)}	—	4.2	—	ns	V _{DD} = 30V, V _{GS} = 10V I _D = 10A, R _g = 4.7Ω
Turn-On Rise Time	t _R	—	13	—		
Turn-Off Delay Time	t _{D(OFF)}	—	27.5	—		
Turn-Off Fall Time	t _F	—	15.3	—		
Body Diode Reverse Recovery Time	t _{RR}	—	20.8	—	ns	I _F = 20A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	13.9	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

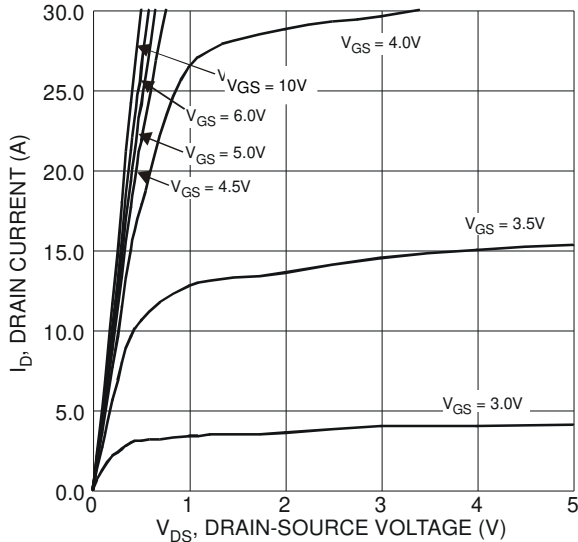


Figure 1 Typical Output Characteristics

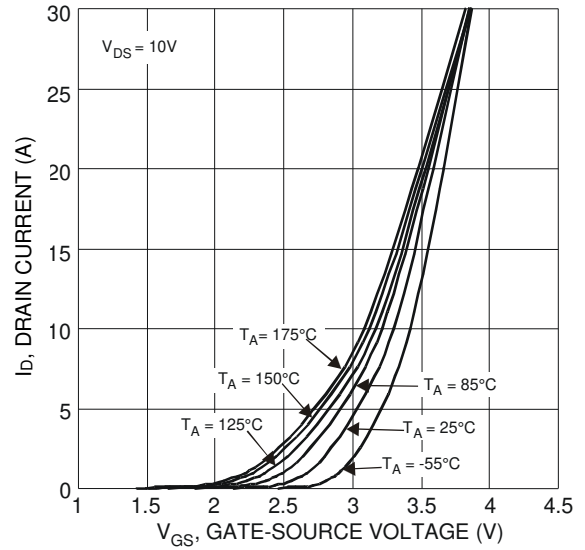


Figure 2 Typical Transfer Characteristics

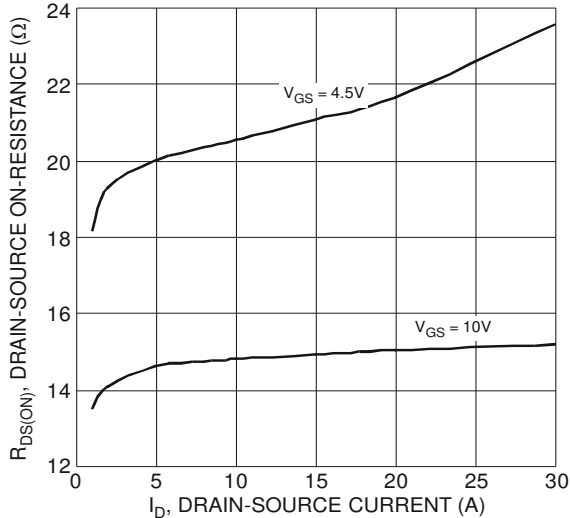


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

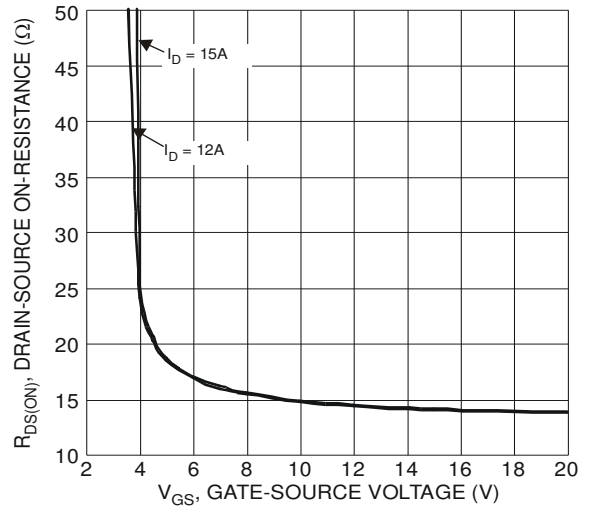


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

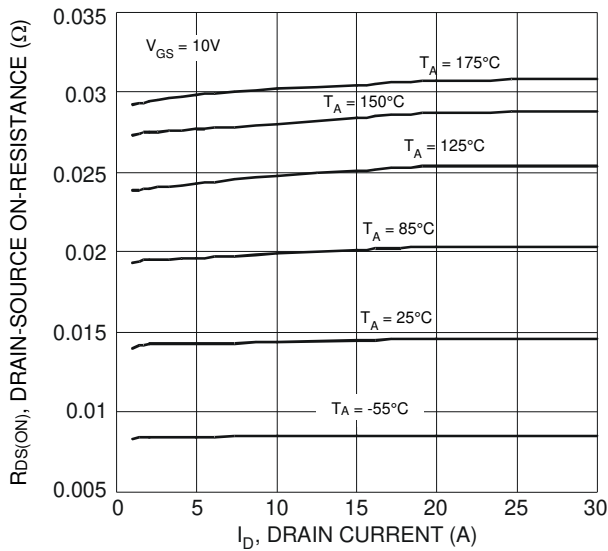


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

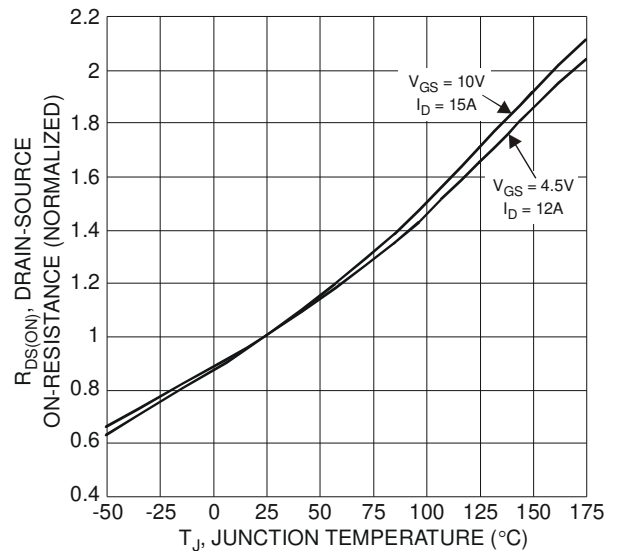


Figure 6 On-Resistance Variation with Temperature

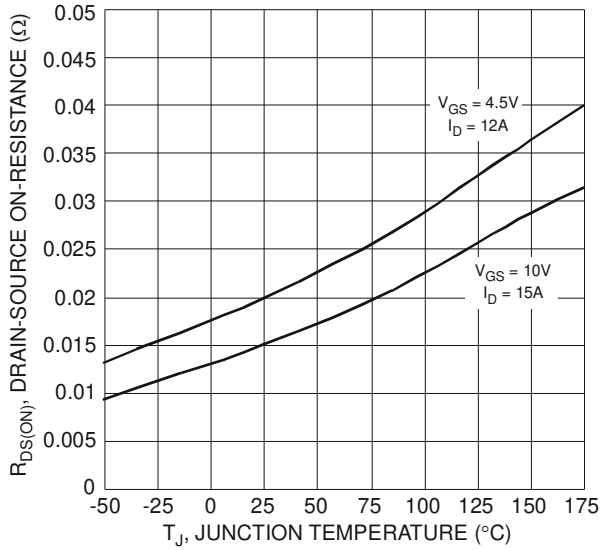


Figure 7 On-Resistance Variation with Temperature

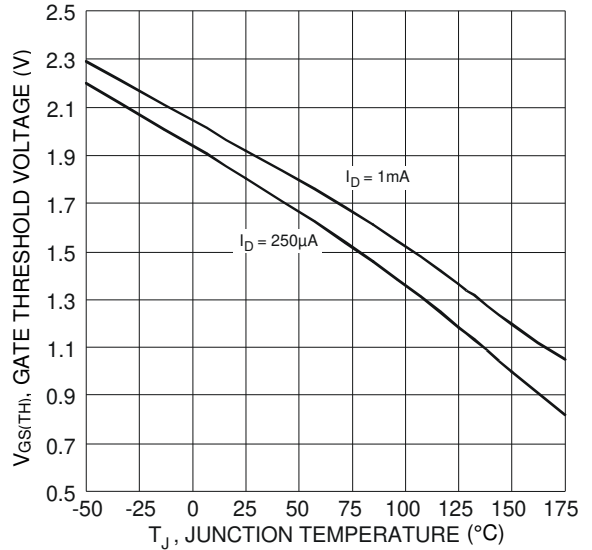


Figure 8 Gate Threshold Variation vs. Junction Temperature

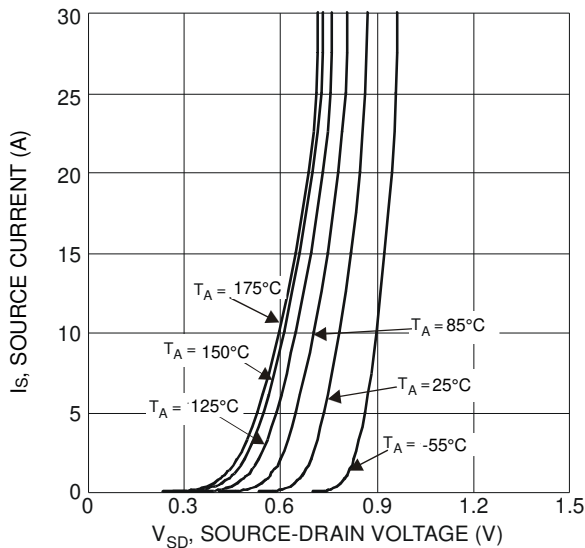


Figure 9 Diode Forward Voltage vs. Current

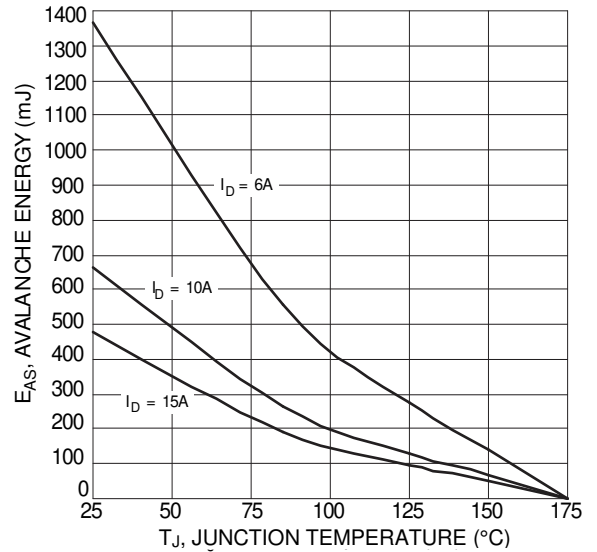


Figure 10 Avalanche Energy

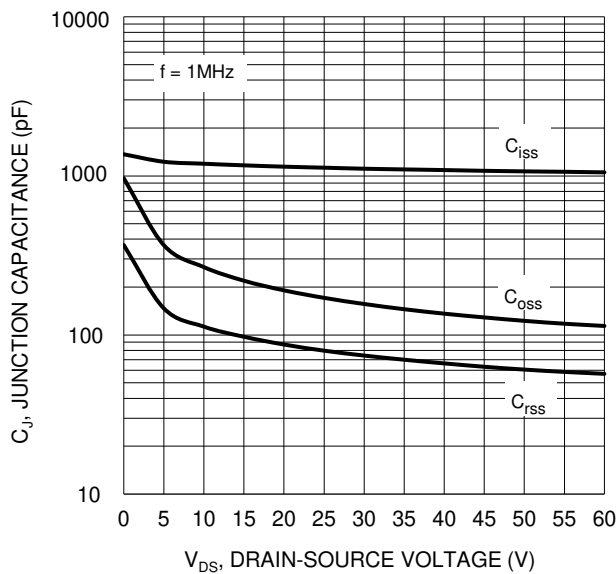


Figure 11 Typical Junction Capacitance

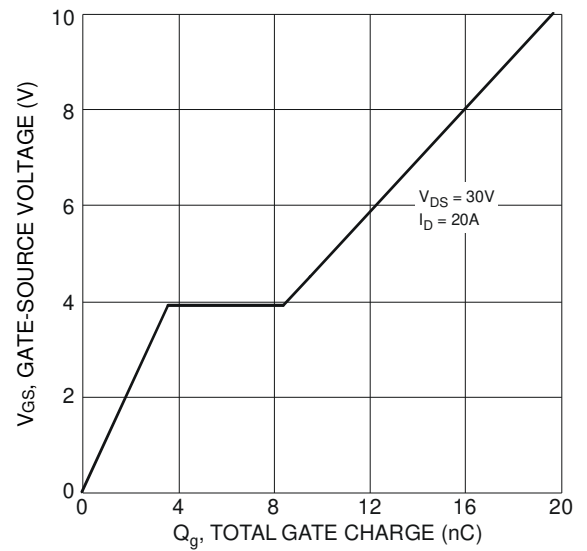


Figure 12 Gate Charge

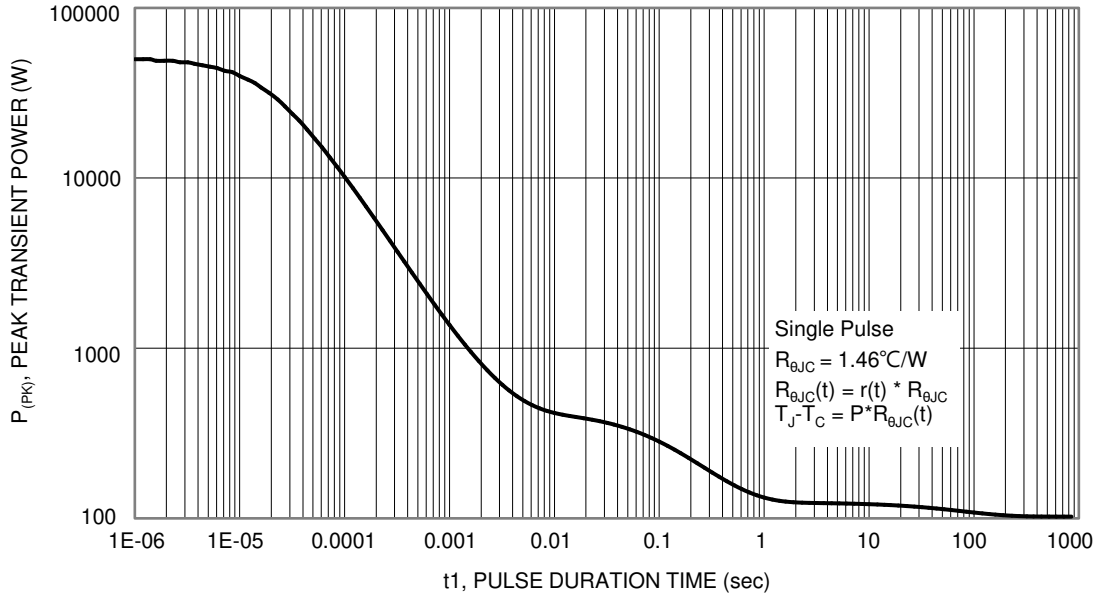


Figure 13 Single Pulse Maximum Power Dissipation

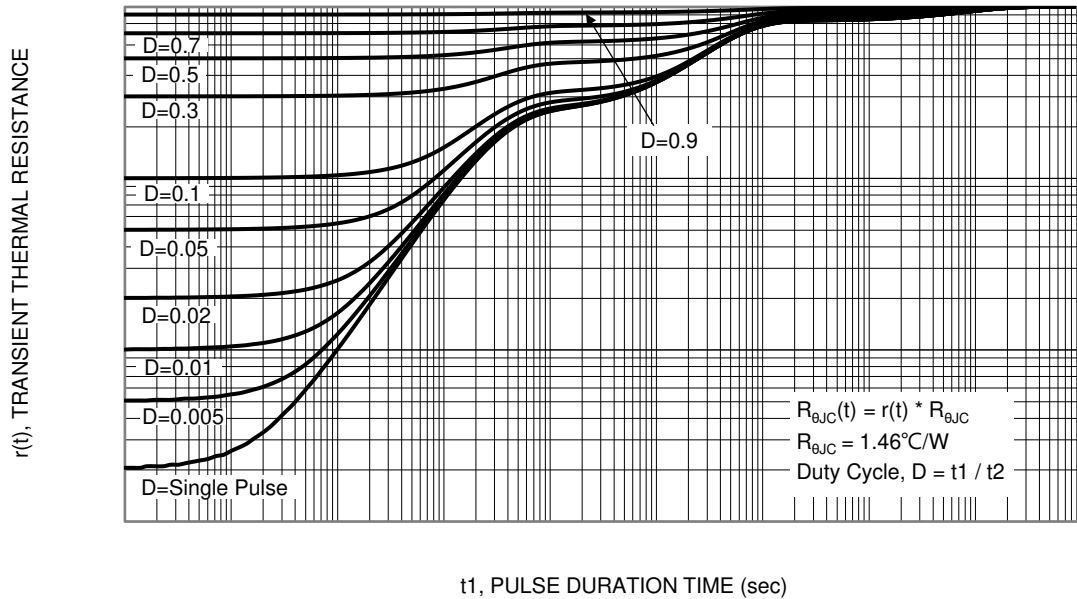


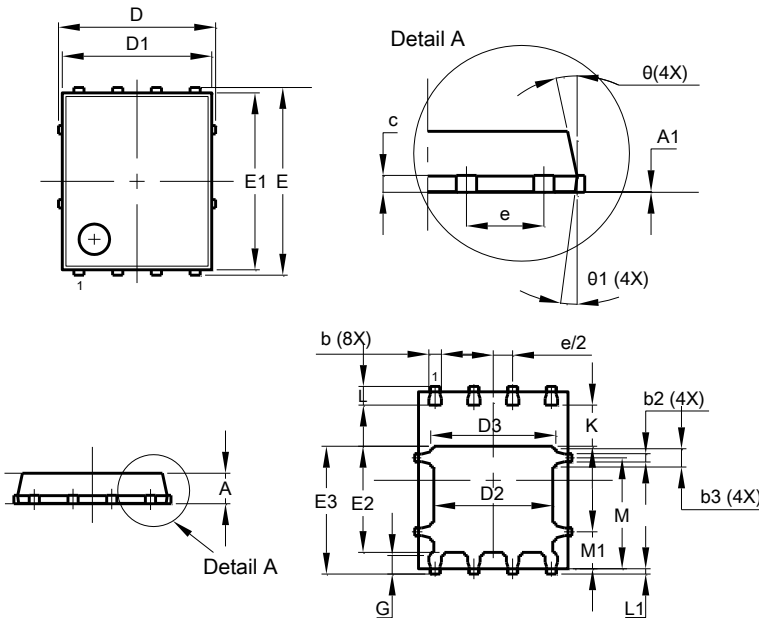
Figure 14 Transient Thermal Resistance

Package Outline

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

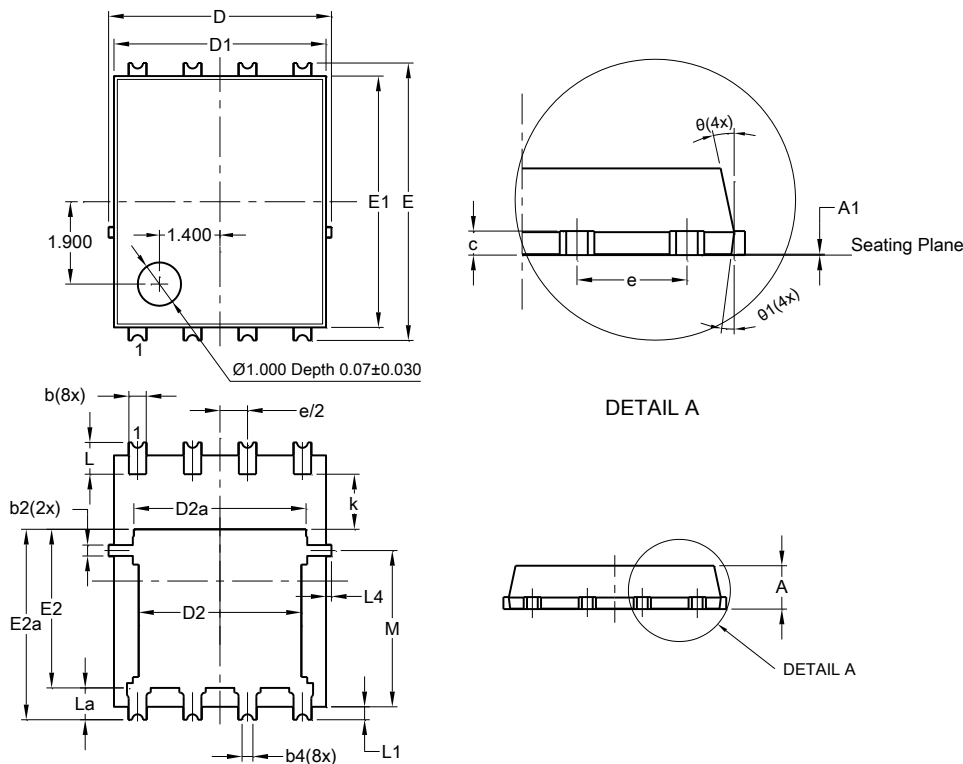
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Site 2:

PowerDI5060-8/SWP (Type UX)



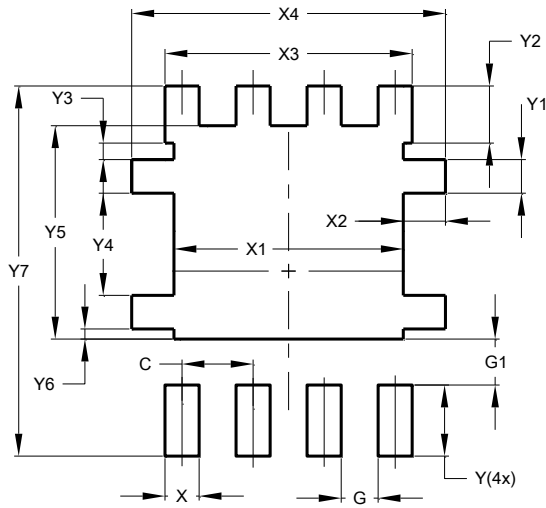
PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

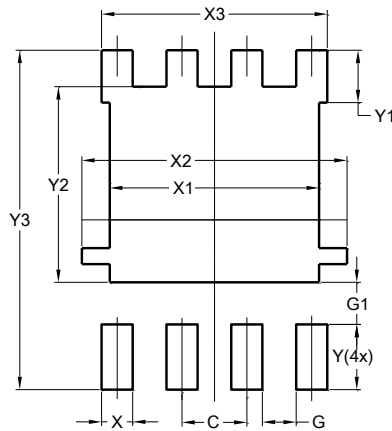
PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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